



TSM2328 100V N-Channel MOSFET



SOT-23

1. Gate 2. Source 3. Drain

Pin Definition:

PRODUC	T SUMMARY

V _{DS} (V)	R _{DS(on)} (mΩ)	I _D (A)
100	250 @ V _{GS} =10V	1.5

General Description

The TSM2328 utilized advanced processing techniques to achieve the lowest possible On-Resistance, extremely efficient and cost-effectiveness device.

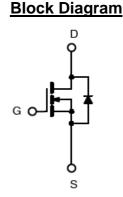
The TSM2328 is universally used for all commercial-industrial applications

Features

- Low $R_{DS(ON)}$ 250m Ω (Max.)
- Low gate charge typical @ 11.1nC (Typ.)
- High performance trench technology

Ordering Information

Part No.	Package	Packing
TSM2328CX RF	SOT-23	3Kpcs / 7" Reel



N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Symbol	Limit	Unit	
V _{DS}	100	V	
V _{GS}	±20	V	
I _D	1.5	А	
I _{DM}	6	А	
I _S	0.6	А	
P _D	1.38	W	
TJ	150	°C	
T _{STG}	-55 to +150	°C	
	V _{DS} V _{GS} I _D I _{DM} I _S P _D T _J	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	

* Limited by maximum junction temperature

Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Foot	RƏ _{JF}	55	°C/W
Thermal Resistance - Junction to Ambient	RƏ _{JA}	100	°C/W

Note 1: Surface mounted on 1" x 1" FR4

Note 2: Pules width limited by maximum junction temperature



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Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV _{DSS}	100			V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 1.5A$	R _{DS(ON)}			250	mΩ
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \text{uA}$	V _{GS(TH)}	1.0		2.5	V
Zero Gate Voltage Drain Current	$V_{DS} = 80V, V_{GS} = 0V$	I _{DSS}			1	uA
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
On-State Drain Current	$V_{DS} = 5V, V_{GS} = 10V$	I _{D(ON)}	6			Α
Forward Transfer Conductance	$V_{DS} = 15V, I_D = 1.5A$	g _{fs}		4		S
Diode Forward Voltage	$I_{\rm S} = 1 {\rm A}, V_{\rm GS} = 0 {\rm V}$	V _{SD}		1.2		V
Dynamic ⁽¹⁾				•	•	
Total Gate Charge		Qg		11.1		nC
Gate-Source Charge	$V_{DS} = 80V, I_D = 1.5A,$	Q _{gs}		4.4		
Gate-Drain Charge	$-V_{GS} = 5V$	Q _{gd}		3		
Input Capacitance		C _{iss}		975		
Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$	C _{oss}		38		pF
Reverse Transfer Capacitance	f = 1.0MHz	C _{rss}		27		1
Switching ⁽²⁾			•	•	•	•
Turn-On Delay Time		t _{d(on)}		9		
Turn-On Rise Time	$V_{DD} = 30V, I_D = 1A,$	t _r		9.4		
Turn-Off Delay Time	V _{GEN} = 10V, R _L =30Ω, - R _G =6Ω	t _{d(off)}		26.8		nS
Turn-Off Fall Time		t _f		2.6		

Electrical Specifications (Ta = 25°C unless otherwise noted)

Note 1: Pulse test: pulse width ≤300uS, duty cycle ≤2%

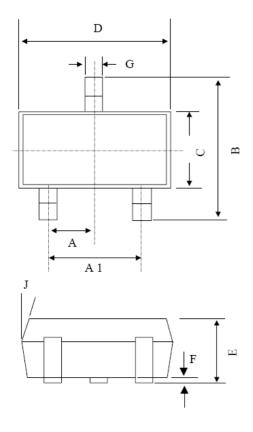
Note 2: Guaranteed by design, not subject to production testing

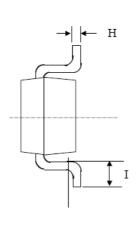


Preliminary

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SOT-23 Mechanical Drawing





SOT-23 DIMENSION					
DIM	MILLIMETERS		INCHES		
DIIVI	MIN	MAX	MIN	MAX.	
Α	0.95 BSC		0.037 BSC		
A1	1.9 BSC		0.074 BSC		
В	2.60	3.00	0.102	0.118	
С	1.40	1.70	0.055	0.067	
D	2.80	3.10	0.110	0.122	
E	1.00	1.30	0.039	0.051	
F	0.00	0.10	0.000	0.004	
G	0.35	0.50	0.014	0.020	
Н	0.10	0.20	0.004	0.008	
I	0.30	0.60	0.012	0.024	
J	5°	10º	5°	10º	



Preliminary

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